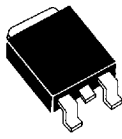




CJD340 NPN
CJD350 PNP

COMPLEMENTARY SILICON
POWER TRANSISTOR

DPAK POWER!TM



DPAK CASE



DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD340, CJD350 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for high voltage general purpose applications.

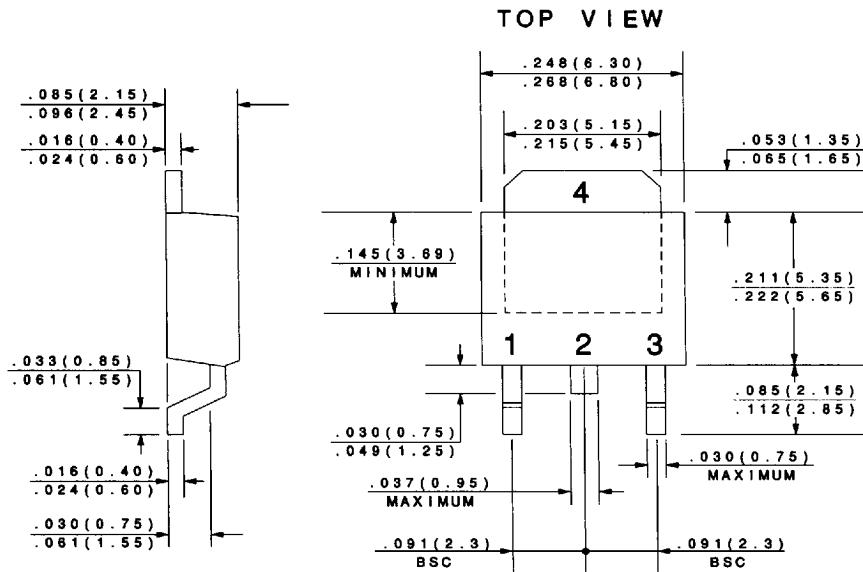
MAXIMUM RATINGS (T_C=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	300	V
Collector-Emitter Voltage	V _{CE0}	300	V
Emitter-Base Voltage	V _{EBO}	3.0	V
Continuous Collector Current	I _C	500	mA
Peak Collector Current	I _{CM}	750	mA
Power Dissipation (T _C =25°C)	P _D	15	W
Power Dissipation (T _A =25°C)	P _D	1.56	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JC}	8.33	°C/W
Thermal Resistance	Θ _{JA}	80.1	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =300V		100	μA
I _{EBO}	V _{EB} =3.0V		100	μA
BV _{CEO}	I _C =1.0mA	300		V
h _{FE}	V _{CE} =10V, I _C =50mA	30	240	

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

DATA
SHEET

R1

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